

# SKM 75GD123D



**SEMITRANS® 6**

## IGBT Modules

SKM 75GD123DL

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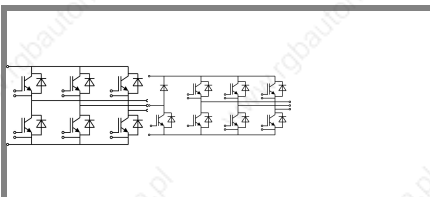
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### Features

- MOS input (voltage controlled)
- N channel, homogeneous Si
- Low inductance case
- Very low tail current with low temperature dependence
- High short circuit capability, self limiting to  $6 \times I_{Cnom}$
- Latch-up free
- Fast & soft inverse Cal diodes
- Isolated copper baseplate using DCB Direct Bonding Technology
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### Typical Applications\*

- Switched mode power supplies
- DC servo and robot drives
- Three phase inverters for AC motor speed control
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Absolute Maximum Ratings		$T_c = 25^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	Values			Units
<b>IGBT</b>					
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200			V
$I_C$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	75		A
		$T_{case} = 80^\circ\text{C}$	50		A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	100			A
$V_{GES}$		$\pm 20$			V
$t_{psc}$	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10			$\mu\text{s}$
<b>Inverse Diode</b>					
$I_F$	$T_j = 150^\circ\text{C}$	$T_{case} = 25^\circ\text{C}$	75		A
		$T_{case} = 80^\circ\text{C}$	50		A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	100			A
$I_{FSM}$	$t_p = 10\text{ ms}; \sin.$	$T_j = 150^\circ\text{C}$	550		A
<b>Module</b>					
$I_{t(RMS)}$		100			A
$T_{vj}$		- 40 ... + 150			$^\circ\text{C}$
$T_{stg}$		- 40 ... + 125			$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500			V

Characteristics		$T_c = 25^\circ\text{C}$ , unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
<b>IGBT</b>						
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2\text{ mA}$	4,5	5,5	6,5	V	
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25^\circ\text{C}$	0,4		1,2	mA
		$T_j = 125^\circ\text{C}$	1,4		1,6	V
$V_{CE0}$			1,6	1,8	V	
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	22		28	$\text{m}\Omega$
		$T_j = 125^\circ\text{C}$	30		38	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_j = ^\circ\text{C}_{chiplev.}$	2,5		3	V
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	3,3		4,3	nF
$C_{oes}$			0,5		0,6	nF
$C_{res}$			0,22		0,3	nF
$t_{d(on)}$	$R_{Gon} = 22\ \Omega$	$V_{CC} = 600\text{ V}$ $I_C = 50\text{ A}$	44		100	ns
$t_r$			56		100	ns
$E_{on}$			8			mJ
$t_{d(off)}$	$R_{Goff} = 22\ \Omega$	$T_j = 125^\circ\text{C}$ $V_{GE} = \pm 15\text{ V}$	380		500	ns
$t_f$			70		100	ns
$E_{off}$			5			mJ
$R_{th(j-c)}$	per IGBT	0,32			K/W	

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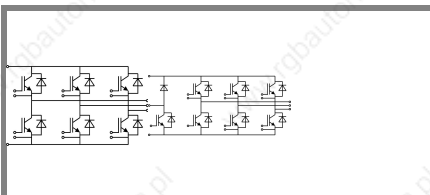
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**GD GD**

### Characteristics

Symbol	Conditions	min.	typ.	max.	Units
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	2	2,5	V
		$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,8		V
$V_{F0}$		$T_j = 25 \text{ }^\circ\text{C}$	1,1	1,2	V
		$T_j = 125 \text{ }^\circ\text{C}$			V
$r_F$		$T_j = 25 \text{ }^\circ\text{C}$	18	26	mΩ
		$T_j = 125 \text{ }^\circ\text{C}$			mΩ
$I_{RRM}$	$I_F = 50 \text{ A}$	$T_j = 125 \text{ }^\circ\text{C}$	35		A
$Q_{rr}$	$di/dt = 800 \text{ A}/\mu\text{s}$		7		μC
$E_{rr}$	$V_{GE} = 0 \text{ V}; V_{CC} = 600 \text{ V}$		2,2		mJ
$R_{th(j-c)D}$	per diode			0,6	K/W
<b>Module</b>					
$L_{CE}$				60	nH
$R_{th(c-s)}$	per module			0,05	K/W
$M_s$	to heat sink M5				Nm
$M_t$	to terminals	4		5	Nm
w				175	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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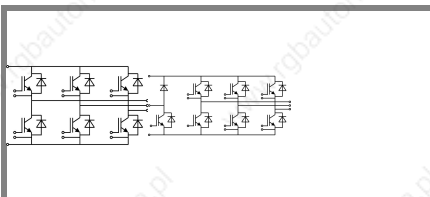
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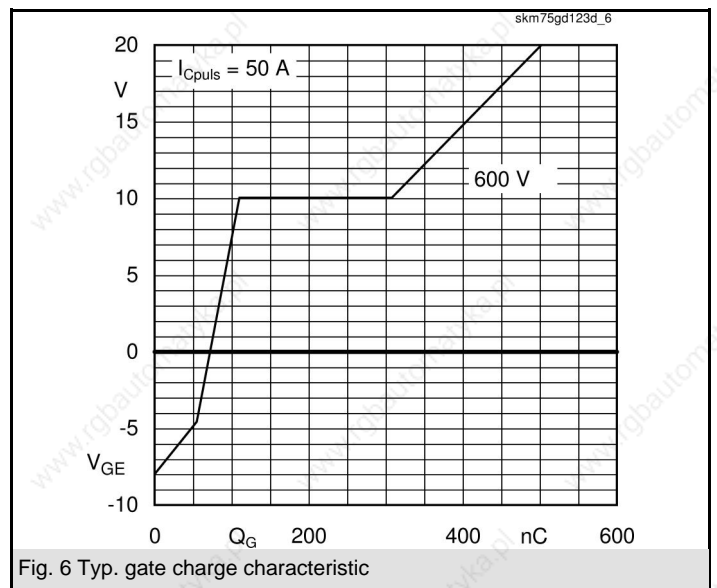
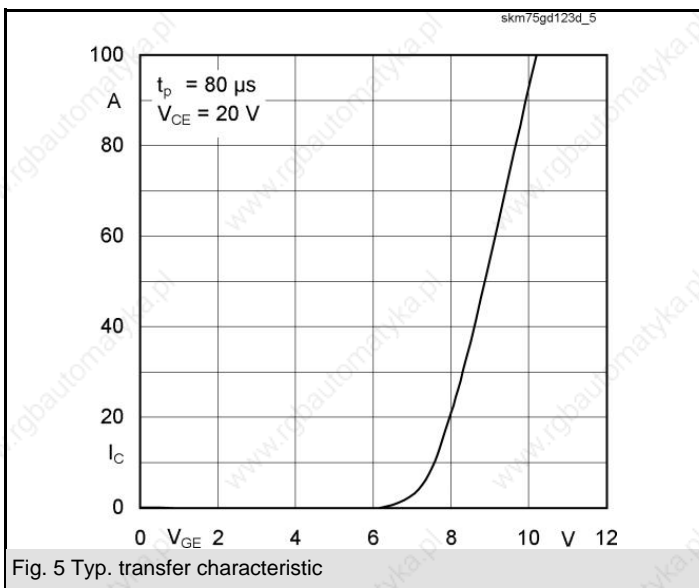
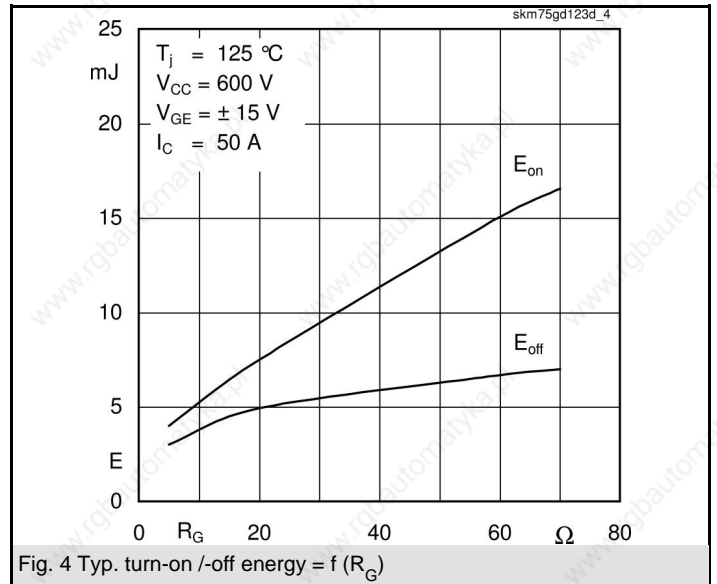
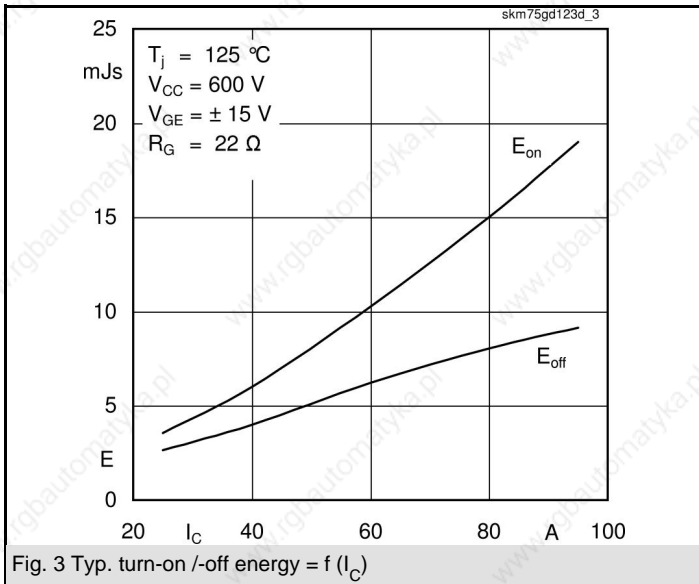
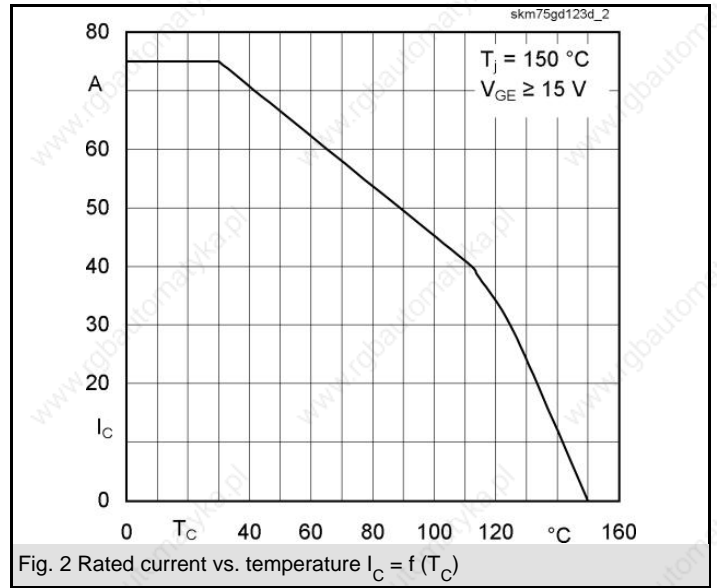
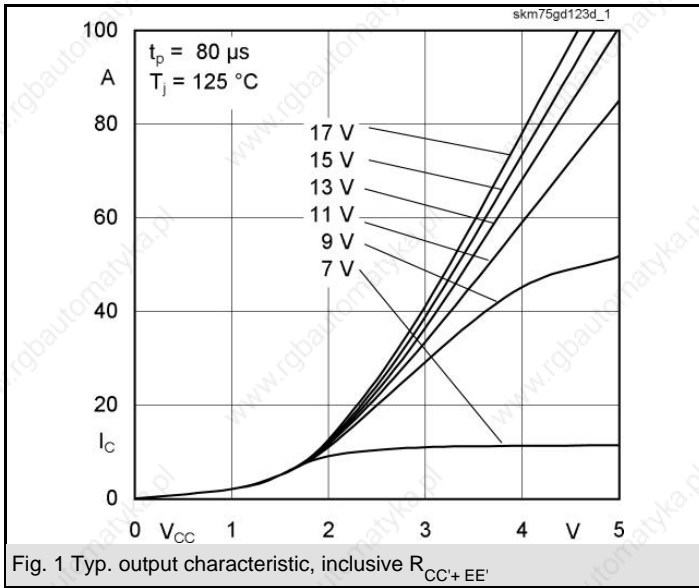


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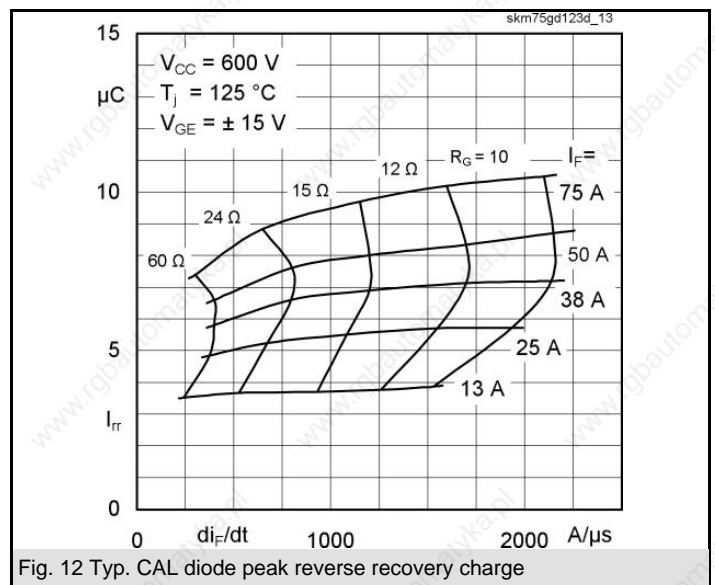
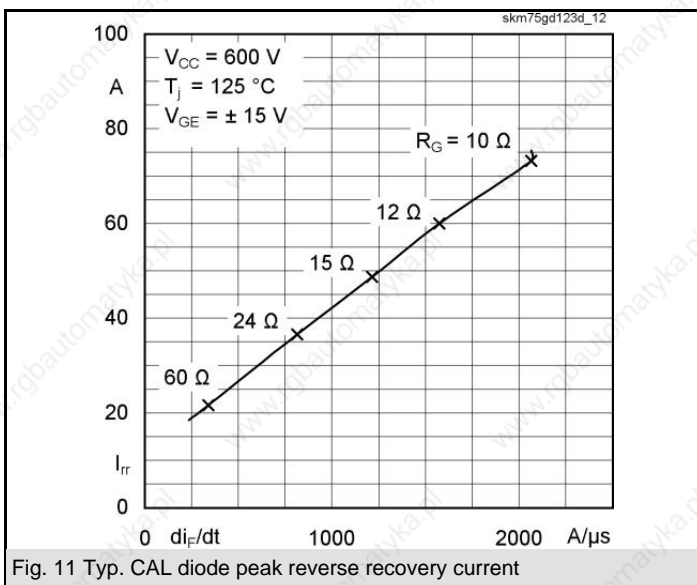
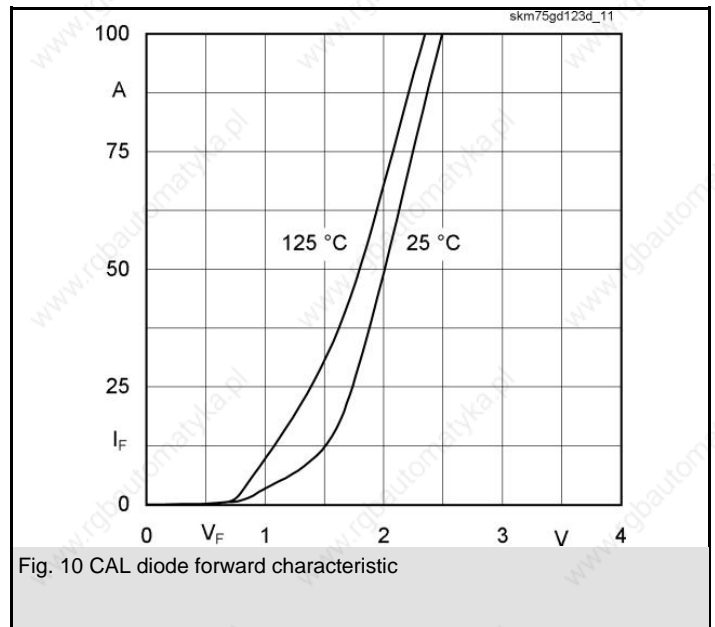
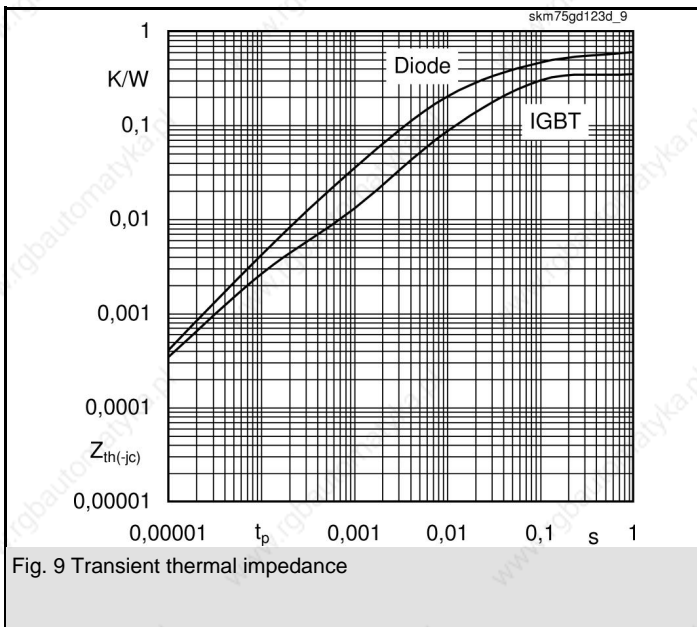
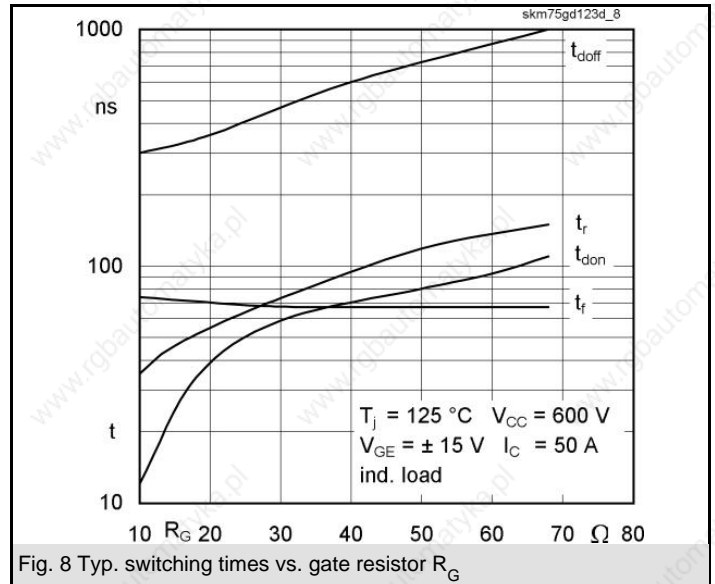
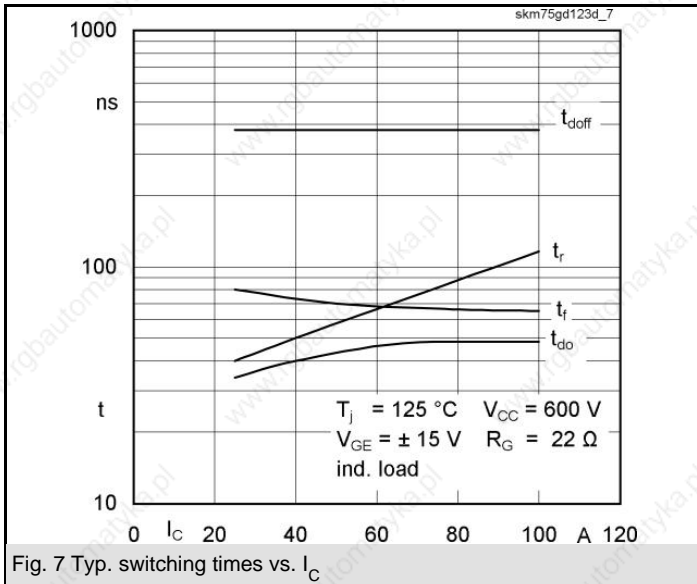
GDL

$Z_{th}$ Symbol	Conditions	Values	Units
<b><math>Z_{th(j-c)}</math></b>			
$R_{\theta j-c}$	$i = 1$	240	mk/W
$R_{\theta j-c}$	$i = 2$	68	mk/W
$R_{\theta j-c}$	$i = 3$	9,2	mk/W
$R_{\theta j-c}$	$i = 4$	2,8	mk/W
$\tau_{th j-c}$	$i = 1$	0,06	s
$\tau_{th j-c}$	$i = 2$	0,0228	s
$\tau_{th j-c}$	$i = 3$	0,0013	s
$\tau_{th j-c}$	$i = 4$	0,0002	s
<b><math>Z_{th(j-c)D}</math></b>			
$R_{\theta j-cD}$	$i = 1$	400	mk/W
$R_{\theta j-cD}$	$i = 2$	168	mk/W
$R_{\theta j-cD}$	$i = 3$	28	mk/W
$R_{\theta j-cD}$	$i = 4$	4	mk/W
$\tau_{th j-cD}$	$i = 1$	0,0831	s
$\tau_{th j-cD}$	$i = 2$	0,0112	s
$\tau_{th j-cD}$	$i = 3$	0,0013	s
$\tau_{th j-cD}$	$i = 4$	0,08	s

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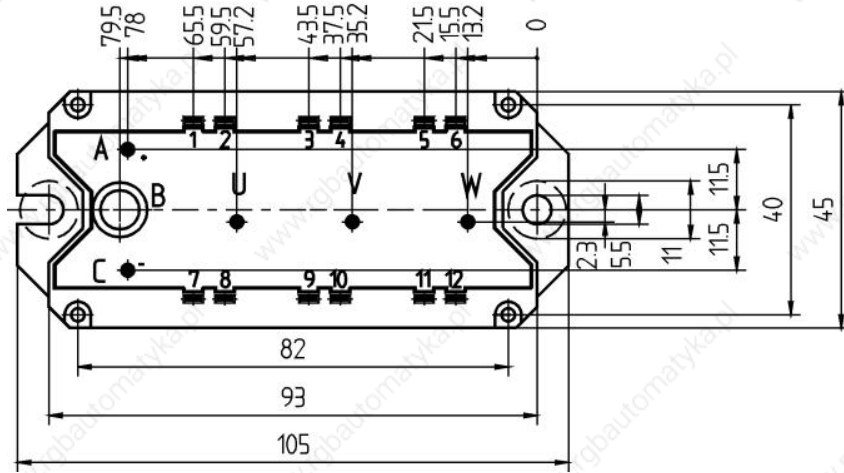
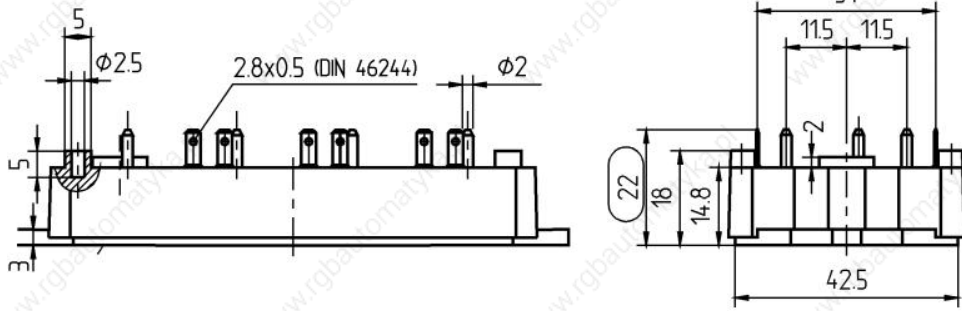


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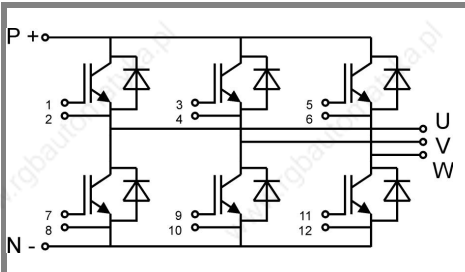
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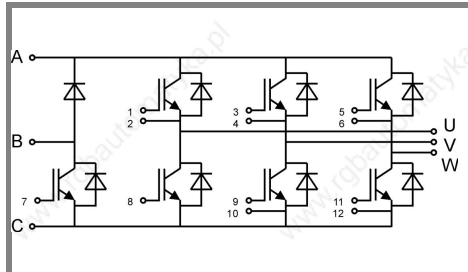


Case D 56a



Case D 67

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Case D 73

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